NPN RF TRANSISTOR

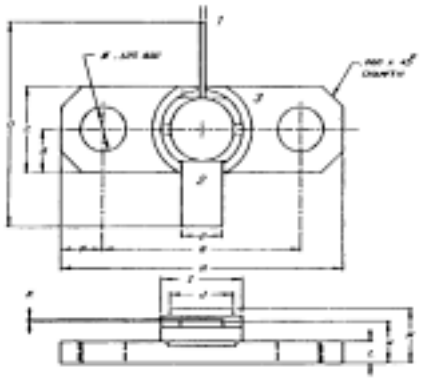
DESCRIPTION:

The **ASI MSC85623** is a Silicon NPN Microwave Transistor Supplied in a Common Base Package, Designed for RF Amplifier and Oscillator Applications up to 3.0 GHz.

MAXIMUM RATINGS

I_C	150 mA
V_{CEO}	14 V
V_{CB}	40 V
V_{EB}	3.5 V
P_{DISS}	25 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	7.0 °C/W

PACKAGE 230 2L FLG



1 = Collector 2 = Emitter
3 = Base

	Minimum Inches/mm	Maximum Inches/mm
A	.025/0.64	.035/0.89
B	.115/2.92 BSC	
C	.225/5.72	.235/5.97
D	.720/18.29	.750/19.05
E	.110/2.79	.120/3.05
F	.120/3.05 BSC	
G	.555/14.10	.565/14.35
H	.795/20.19	.805/20.45
I	.222/5.64	.236/5.99
J	.165/4.19	.180/4.57
K	.002/0.05	.007/0.18
L	.055/1.40	.067/1.70
M	.120/3.18	.140/3.56
N		.170/4.32

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5.0 mA	14			V
BV_{CER}	I_C = 5.0 mA R_{BE} = 510 Ω	30			V
BV_{CBO}	I_C = 5.0 mA	40			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CBO}	V_{CB} = 21 V			2.0	mA
P_G	V_{CC} = 28 V P_{out} = 5.0 W f = 3.0 GHz		5.5		dB
η_C			30		%